MR820, MR821, MR822, MR824, MR826

Designers Data Sheet

SUBMINIATURE SIZE, AXIAL LEAD MOUNTED **FAST RECOVERY POWER RECTIFIERS**

. . . designed for special applications such as dc power supplies, inverters, converters, ultrasonic systems, choppers, low RF interference and free wheeling diodes. A complete line of fast recovery rectifiers having typical recovery time of 100 nanoseconds providing high efficiency at frequencies to 250 kHz.

Designer's Data for "Worst Case" Conditions

The Designers Data sheets permit the design of most circuits entirely from the information presented. Limit curves - representing boundaries on device characteristics - are given to facilitate "worst case" design.

MAXIMUM RATINGS

Rating	Symbol	MR820	MR821	MR822	MR824	MR826	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	VRRM VRWM VR	50	100	200	400	600	Volts
Non-Repetitive Peak Reverse Voltage	VRSM	75	150	250	450	650	Volts
RMS Reverse Voltage	VR(RMS)	35	. 70	140	280	420	Volts
Average Rectified Forward Current (Single phase, resistive load, TA = 55°C) (1)	10	5.0				Amp	
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions)	IFSM	300					Amp
Operating and Storage Junction Temperature Range (2)	T _J ,T _{stg}	-		-65 to +17!	5 ——		°c

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit			
Thermal Resistance, Junction to Ambient	R _{eJA}	25	oc.w			
(Recommended Printed Circuit Board		i				
Mounting See Note 6 Page 8)		l				

ELECTRICAL CHARACTERISTICS

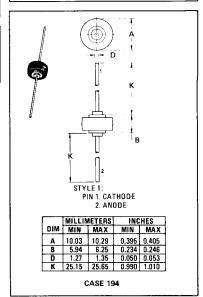
Characteristic	Symbol	Min	Тур	Max	Unit
Instantaneous Forward Voltage (Ip = 15.7 Amp, Tj = 150°C)	٧F	_	0.75	1.05	Volts
Forward Voltage (IF = 5.0 Amp, T _J = 25°C)	VF	_	0.9	1.0	Volts
Maximum Reverse Current, (rated dc voltage) Tj = 25°C Tj = 100°C	I _R	- -	5.0 0.5	25 1.0	μA mA

REVERSE RECOVERY CHARACTERISTICS

Characteristic	Symbol	Min	Тур	Mex	Unit
Reverse Recovery Time	tre				ns
(IF = 1.0 Amp to VR = 30 Vdc, Figure 25)	"	_	100	200	
(I _{FM} = 15 Amp, di/dt = 25 A/µs, Figure 26)		-	150	300	
Reverse Recovery Current	RM(REC)				Amp
(IF = 1.0 Amp to VR = 30 Vdc, Figure 25)		-	-	2.0	

(1) Must be derated for reverse power dissipation. See Note 3 (2) Derate as shown in Figure 1.

FAST RECOVERY POWER RECTIFIERS 50-600 VOLTS **5.0 AMPERES**



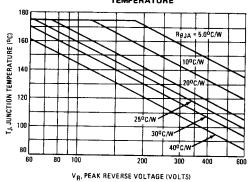
MECHANICAL CHARACTERISTICS

CASE: Void Free, Transfer Molded FINISH: External Surfaces are Corrosion Resistant POLARITY: Indicated by Diode Symbol WEIGHT: 2.5 Grams (Approximately) MAXIMUM LEAD TEMPERATURE FOR SOLDERING PURPOSES: 350°C, 3/8" from case for 10 s

at 5.0 lb. tension.,

MAXIMUM CURRENT AND TEMPERATURE RATINGS

FIGURE 1 — MAXIMUM ALLOWABLE JUNCTION TEMPERATURE



NOTE 1 MAXIMUM JUNCTION TEMPERATURE DERATING

When operating this rectifier at junction temperatures over approximately 85°C, reverse power dissipation and the possibility of thermal runaway must be considered. The data of Figure 1 is based upon worst case reverse power and should be used to derate T_{J(max)} from its maximum value of 175°C. See Note 3 for additional information on derating for reverse power dissipation.

When current ratings are computed from $T_{J(max)}$ and reverse power dissipation is also included, ratings vary with reverse voltage as shown on Figures 2 thru 5.

RESISTIVE LOAD RATINGS PRINTED CIRCUIT BOARD MOUNTING - SEE NOTE 6, PAGE 8

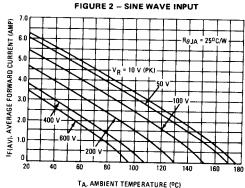
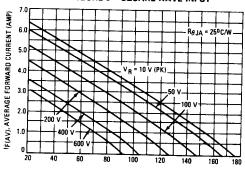
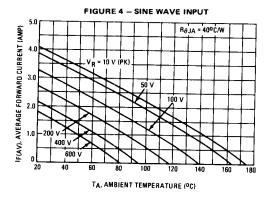
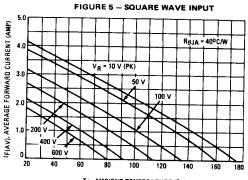


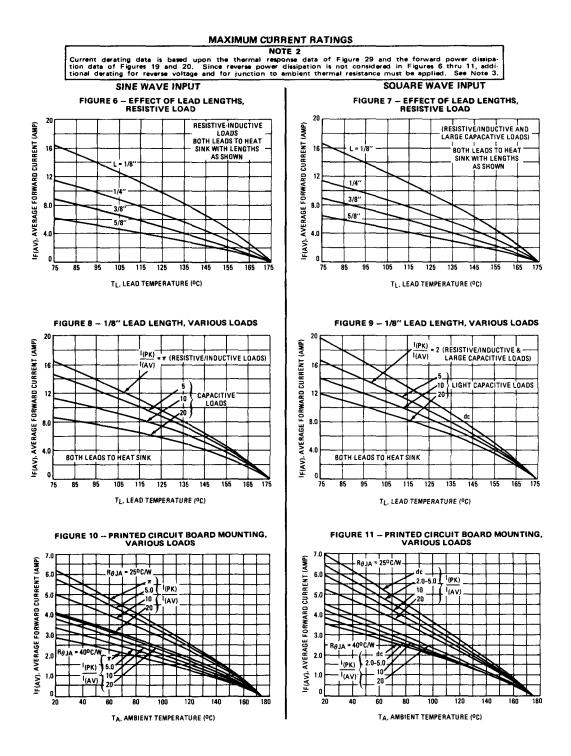
FIGURE 3 - SQUARE WAVE INPUT



TA, AMBIENT TEMPERATURE (°C)







REVERSE POWER DISSIPATION AND CURRENT

NOTE 3

DERATING FOR REVERSE POWER DISSIPATION

In this rectifier, power loss due to reverse current is generally not negligible. For reliable circuit design, the maximum junction emperature must be limited to either 175°C or the temperature which results in thermal runaway. Proper derating may be accomplished by use of equation 1 or equation 5.

Equation 1 TA = T1 - (175 - TJ(max)) - PR RBJA

 T_1 = Maximum Allowable Ambient Temperature neglecting reverse power dissipation (from Figures 10 or 11)

 $T_{J(max)}$ * Maximum Allowable Junction Temperature to prevent thermal runeway or 175°C, which ever is lower. (See Figure 1).

 P_R = Reverse Power Dissipation (From Figure 12 or 13, adjusted for $T_{J(max)}$ as shown below)

Rela * Thermal Resistance, Junction to Ambient

When thermal resistance, junction to ambient, is over 20°C/W, the effect of thermal response is negligible. Satisfactory derating may be found by using:

Equation 2 TA = TJ(max) - (PR + PF) ReJA

Pp * Forward Power Dissipation (See Figures 19 & 20) Other terms defined above.

The reverse power given on Figures 12 and 13 is calculated for $T_J=150^{\circ}C$. When T_J is lower, Pg will decrease; its value can be found by multiplying Pg by the normalized reverse current from Figure 14 at the temperature of interest.

The reverse power data is calculated for half wave rectification circuits. For full wave rectification using either a bridge or a center-tapped transformer, the data for resistive loads is equiva-

lent when Vp is the line to line voltage across the rectifiers. For capacitive loads, it is recommended that the dc case on Figure 13 be used, regardless of input waveform, for bridge circuits. For capacitively loaded full wave center-tapped circuits, the 20:1 data of Figure 12 should be used for sine wave inputs and the capacitive load data of Figure 13 should be used for square wave inputs regardless of $\{|p_k\rangle/|(a_v)\}$. For these two cases, Vp is the voltage across one leg of the transformer.

Find Maximum Ambient Temperature for I_{AV} = 2 A, Capacitive Load of I_{PK}/I_{AV} = 20, Input Voltage = 120 V (rms) Sine Wave, $R_{\theta,JA} \simeq 25^{\circ} C/W$, Half Wave Circuit.

Solution 1:

Step 1: Find Vp; Vp = $\sqrt{2}$ V_{in} = 169 V, VR(pk) = 338 V Step 2: Find TJ(max) from Figure 1. Read TJ(max) = 119°C. Step 3: Find PR(max) from Figure 12. Read PR = 770 mW @ 140°C Step 4: Find IR normalized from Figure 14. Read IR(norm) = 0.4

Step 5: Correct PR to T J(max): PR = IR(norm) × PR (Figure 12)

PR = 0.4 × 770 = 310 mW.

Step 6: Find Pr from Figure 19. Read Pr = 2.4 W

Step 7: Compute T_A from T_A = T_{J(max)} · (P_R + P_F) R_{0 JA} T_A = 119 · (0.31 + 2.4) (25) T_A = 51°C

Solution 2:

Solution 2: Step 1 thru 5 are as above. Step 6: Find T_A = T₁ from Figure 10. Read T_A = 115°C. Step 7: Compute T_A from T_A = T₁ - (175 - (17) - (178 - (17) - (0.31)(25)) T_A = 51°C.

T_A = 51°C.

- ashorts will occur because

At times, a discrepancy between methods will occur because thermal response is factored into Solution 2.

FIGURE 12 - SINE WAVE INPUT DISSIPATION

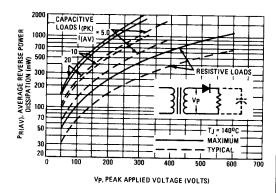
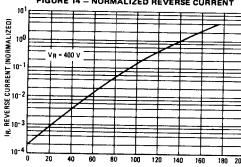


FIGURE 14 - NORMALIZED REVERSE CURRENT



TJ, JUNCTION TEMPERATURE (°C)

FIGURE 13 - SQUARE WAVE INPUT DISSIPATION

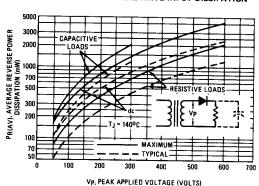
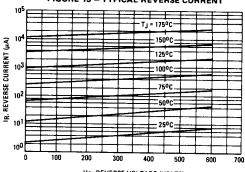
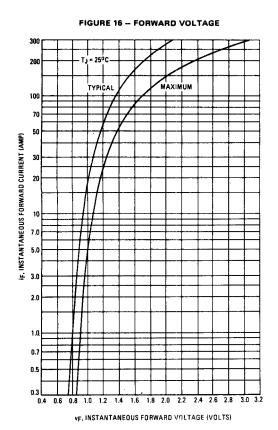


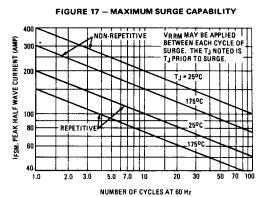
FIGURE 15 - TYPICAL REVERSE CURRENT

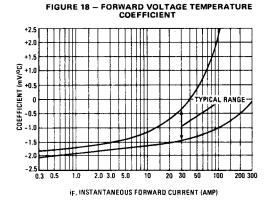


VR, REVERSE VOLTAGE (VOLTS)

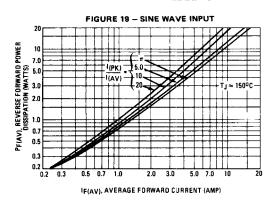
STATIC CHARACTERISTICS

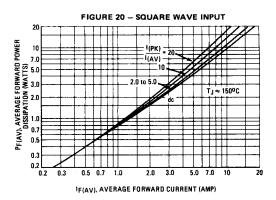




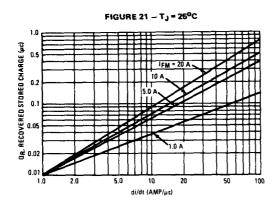


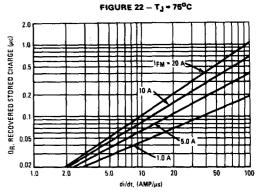
MAXIMUM FORWARD POWER DISSIPATION

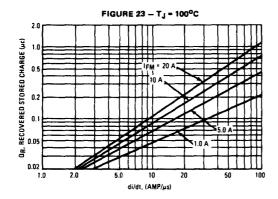


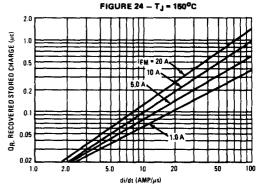


TYPICAL RECOVERED STORED CHARGE DATA (See Note 4)









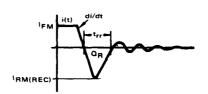
NOTE 4

Reverse recovery time is the period which elapses from the time that the current, thru a previously forward biased rectifier diode, passes thru zero going negatively until the reverse current recovers to a point which is less than 10% peak reverse current.

Reverse recovery time is a direct function of the forward current prior to the application of reverse voltage.

For any given rectifier, recovery time is very circuit dependent. Typical and maximum recovery time of all Motorola fast recovery power rectifiers are rated under a fixed set of conditions using $I_F \simeq 1.0~A,~V_R \simeq 30~V.~In~order~to~cover~all~circuit conditions, curves are given for typical recovered stored charge versus commutation di/dt for various levels of forward current and for junction temperatures of <math display="inline">25^{\rm O}C,~75^{\rm O}C,~100^{\rm O}C,$ and $150^{\rm O}C.$

To use these curves, it is necessary to know the forward current level just before commutation, the circuit commutation di/dt, and the operating junction temperature. The reverse recovery test current waveform for all Motorola fast recovery rectifiers is shown.



From stored charge curves versus di/dt, recovery time $\{t_{ff}\}$ and peak reverse recovery current $\{l_{RM(REC)}\}$ can be closely approximated using the following formulas:

$$t_{rr} = 1.41 \times \left[\frac{Q_R}{di/dt} \right]^{1/2}$$

IRM(REC) = 1.41 x [QR x di/dt] 1/2

DYNAMIC CHARACTERISTICS

FIGURE 25 - REVERSE RECOVERY CIRCUIT

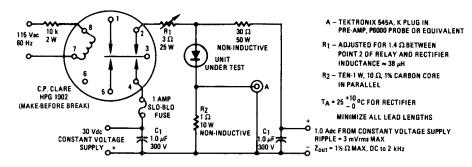
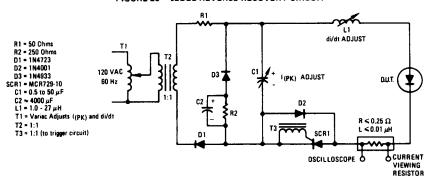
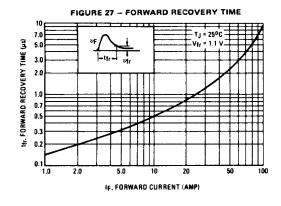
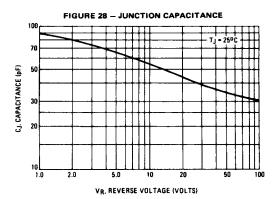


FIGURE 26 - JEDEC REVERSE RECOVERY CIRCUIT

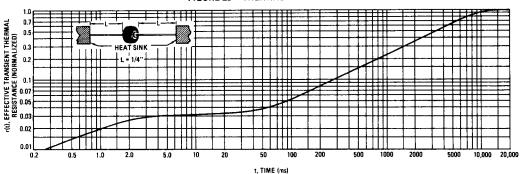






THERMAL CHARACTERISTICS

FIGURE 29 - THERMAL RESPONSE



NOTE 5

To determine maximum junction temperature of the diode in a given situation, the following procedure is recommended:

The temperature of the lead should be measured using a thermocouple placed on the lead as close as possible to the tie point. The thermal mass connected to the tie point is normally large enough so that it will not significantly respond to heat surges generated in the diode as a result of pulsed operation once steady-state conditions are achieved. Using the measured value of $T_{\rm L}$, the junction temperature may be determined by:

$$T_J = T_L + \triangle T_{JL}$$

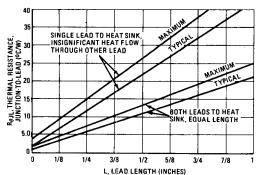
where $\triangle T_{JL}$ is the increase in junction temperature above the lead temperature. It may be determined by:

 Δ T_{JL} = P_{pk} \cdot R_{θ JL} [D + (I - D) \cdot r(t₁ + t_p) + r(t_p) - r(t₁)] where r(t) = normalized value of transient thermal resistance at time t from Figure 29, i.e.:

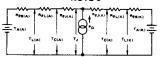
 $r(t_1 \, + \, t_p) \, = \, normalized$ value of transient thermal resistance at time $t_1 + t_p.$



FIGURE 30 - STEADY-STATE THERMAL RESISTANCE



NOTE 6



Use of the above model permits junction to lead thermal resistance for any mounting configuration to be found. Lowest values occur when one side of the rectifier is brought as close as possible to the heat sink as shown below. Terms in the model signify:

 $T_{f A}=Ambient Temperature R_{m{ heta}S}=Thermal Resistance, Heat$ sink to Ambient

T_L = Lead Temperature R₀ L = Thermal Resistance, Lead to Heat Sink

 T_C = Case Temperature $R_{\theta J}$ = Thermal Resistance, Junction to Case

 T_J = Junction Temperature P_D = Power Dissipation = P_F + P_R P_F = Forward Power Dissipation P_R = Reverse Power Dissipation

(Subscripts(A) and(K) refer to anode and cathode sides respectively) Values for thermal resistance components are:

 ${\rm H}_{\theta\perp}$ = 40°C/W/IN. Typically and 44°C/W/IN Maximum. ${\rm H}_{\theta\downarrow}$ = 2°C/W Typically and 4°C/W Maximum.

Since $R_{\theta,J}$ is so low, measurements of the case temperature, T_C , will be approximately equal to junction temperature in practical lead mounted applications. When used as a 60 Hz rectifier, the slow thermal response holds $T_{J/P(N)}$ (lose to $T_{J/Q(N)}$. Therefore maximum lead temperature may be found as follows:

T_L = T_{J(max)} -
$$\Delta$$
T_{JL}

ΔT_{JL} can be approximated as follows:

 $\Delta T_{JL} \approx R_{BJL} \cdot P_D$; P_D is the sum of forward and reverse power dissipation shown in Figures 12 & 19 for sine wave operation and Figures 13 & 20 for square wave operation.

The recommended method of mounting to a P.C. board is shown on the sketch, where $R_{g,j,k}$ is approximately 25°C/W for a 1-1/2" x 1-1/2" copper surface area. Yalues of 40°C/W are typical for mounting to terminal strips or P.C. boards where available surface area is small.

